

REMARKS

Applicants thank the Examiner for allowing claims 55-59 and 63-66.

Applicants have cancelled claims 47-54, 67, 68, 70, 72, 73 and 97 without prejudice to expedite prosecution. Applicants have amended claim 84 to include the limitations of claims 88 and 92. Claim 89 has been amended, and claims 88 and 92 have cancelled to reflect the amendment to claim 84.

Claims 47-54, 67, 68, 70, 72, 73, 84, 85, 87-93 and 97 have been rejected under 35 USC 102(b) or "in the alternative" under 35 USC 103(a) on U.S. Patent No. 4,803,527 (Hatta). Applicants respectfully traverse this rejection.

The rejection of claims 47-54, 67, 68, 70, 72, 73, 88, 92 and 97 is moot in view of the cancellation of these claims.

Claim 84 recites a common input terminal connected to the source or drain electrode of the first transistor and to the source or drain electrode of the second transistor and a protecting element connected between the common input terminal and the first control terminal and states that the protecting element comprises a first high concentration impurity region, a second high concentration impurity region and an insulating region disposed between the first and second high concentration impurity regions and that the first high concentration impurity region is at least part of the first resistor high concentration impurity region. Claim 84 has been amended to state that the common input terminal comprises a bonding pad, a peripheral high concentration impurity region is disposed at a peripheral area of the bonding pad, and the second high concentration impurity region is part of the peripheral high concentration impurity region.

Although the Examiner explained the rejection of claim 67, he did not separately address claim 84, which has claim scope different from claim 67, and their dependent claims. See page 2 of the Action. In rejecting claim 67, the Examiner contends that the device shown in Hatta's FIG. 1 corresponds to the claimed semiconductor device. However, Hatta's FIG. 1 does not disclose the semiconductor switching device of claim 84.

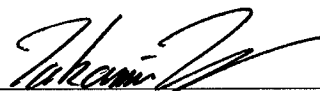
Claim 84 requires that the common input terminal be connected to the source or drain electrode of the first transistor and to the source or drain electrode of the second transistor. It is true that the device shown in Hatta's FIG. 1 includes MESFET Q1 and MESFET Q2. However, it does not include a common input terminal having a bonding pad and connected to the source or the drain of the two transistors. See FIG. 1 of Hatta. The Examiner does not point to any portion of Hatta's device as corresponding to the claimed common input terminal. To the extent that it does not disclose the claimed common input terminal, Hatta fails to disclose the limitation that a peripheral high concentration impurity region is disposed at a peripheral area of the bonding pad of the common input terminal, and the second high concentration impurity region is part of the peripheral high concentration impurity region.

The rejection of claims 84, 85, 87, 89-91 and 93 on Hatta should be withdrawn because Hatta does not teach or suggest the claimed common input terminal.

In the event that the transmittal letter is separated from this document and the Patent and Trademark Office determines that an extension and/or other relief is required, applicants petition for any required relief including extensions of time and authorize the Commissioner to charge the cost of such petitions and/or other fees due in connection with the filing of this document to **Deposit Account No. 03-1952**, referencing Docket No. **492322017300**.

Respectfully submitted,

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